TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode Silicon N-Channel MOS Type (U-MOS V-H)

# TPCA8A02-H

High Efficiency DC-DC Converter Applications
Notebook PC Applications

Portable Equipment Applications

Portable Equipment Applications

- Built-in a schottky barrier diode
   Low forward voltage: V<sub>DSF</sub> = -0.6 V (max)
- · High-speed switching
- Small gate charge: Q<sub>SW</sub> = 8.6 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS (ON)} = 3.8 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: |Y<sub>fs</sub>| = 90 S (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub> <	30	y	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	\\\\	
Gate-source voltage		V <sub>GS</sub> S	±20	V	
Drain current	DC (Note 1)	<del>(</del> )	34	A	
Drain current	Pulsed (Note 1)	((I <sub>DP</sub>	102		
Drain power dissipation	on (Tc=25°C)		45 W		
Drain power dissipation	on (t = 10 s) (Note 2a)	<b> D</b> D  D	2.8	w	
Drain power dissipation (t=10.s) (Note 2b)		PD	1.6	W	
Single-pulse avalanche energy (Note 3)		E <sub>AS</sub>	150	mJ	
Avalanche current		IAR	34	Α	
Repetitive avalanche energy (Tc=25°C) (Note 4)		EAR	3.23	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	–55 to 150	°C	

Note: For Notes 1 to 4, refer to the next page.

Unit: mm

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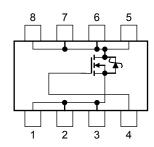
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Weight: 0.069 g (typ.)

### **Circuit Configuration**



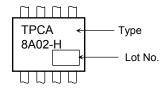
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case (Tc=25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W	
Thermal resistance, channel to ambient $(t=10\;s) \eqno(Note\;2a)$	R <sub>th (ch-a)</sub>	44.6	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W	

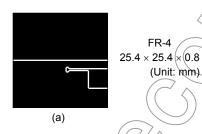
### Marking (Note 5)

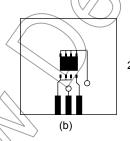


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





FR-4  $25.4 \times 25.4 \times 0.8$  (Unit: mm)

Note 3:  $V_{DD} = 24 \text{ V}$ ,  $V_{Ch} = 25^{\circ}\text{C}$  (initial), L = 0.1 mH,  $R_{G} \neq 25^{\circ}\Omega$ ,  $I_{AR} = 34 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)

Week of manufacture

(01 for first week of year, continuing up to 52 or 53)

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Year of manufacture

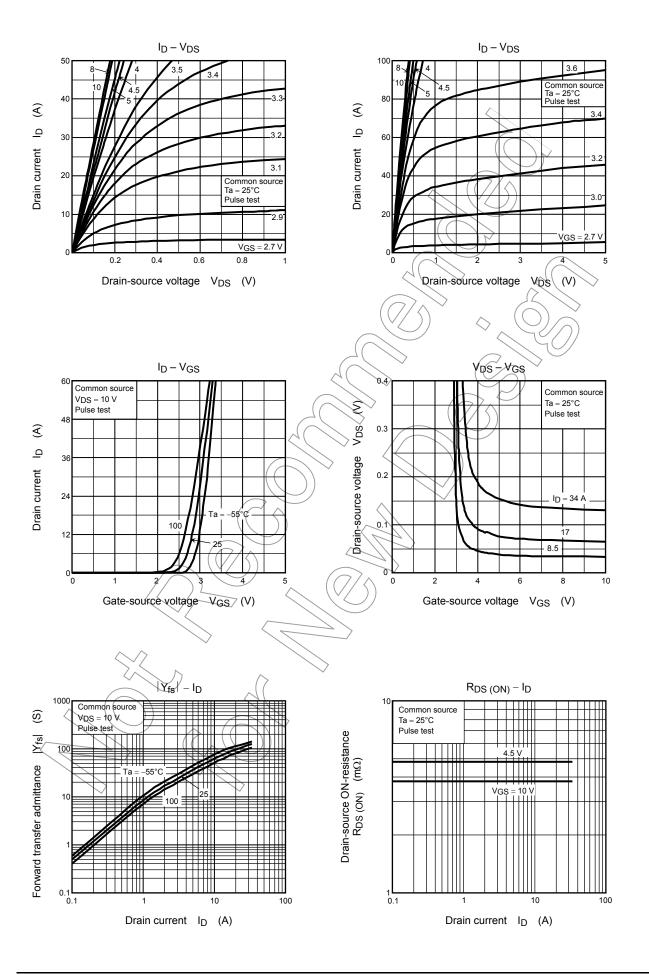
(The last digit of the calendar year)

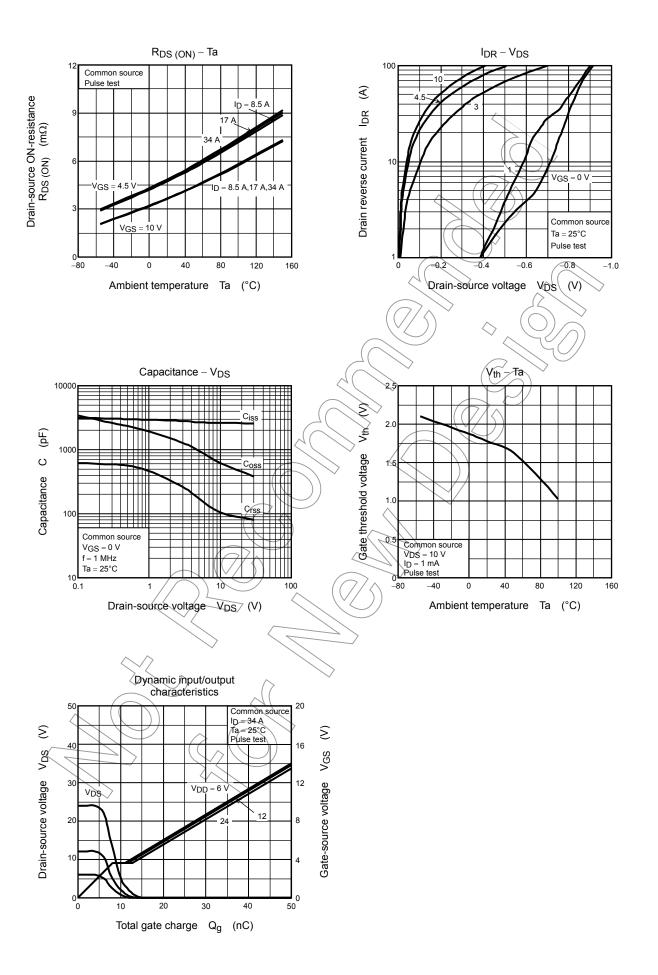
## **Electrical Characteristics (Ta = 25°C)**

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V		_	100	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_		
Gate threshold vo	oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.3	) / _	2.3	V	
Drain-source ON-resistance		Б	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 17 A	<u> </u>	4.8	6.7	m()	
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 17 A	))	3.8	5.3	mΩ	
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 17 A	45	90	_	S	
Input capacitance		C <sub>iss</sub>		<sup>2</sup> —	2640	3430		
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	100	150	pF	
Output capacitan	ce	C <sub>oss</sub>			610	$\nearrow$		
Gate resistance		rg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz	-6	1.0	) 1.5	Ω	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 0 V I <sub>D</sub> = 17 A C C C C C C C C C C C C C C C C C C	7	3.6	) _		
	Turn-on time	t <sub>on</sub>		\(\int\)	12	_	ns	
	Fall time	tf	4. w w o R o O O O O O O O O O O O O O O O O O		7.7	_	115	
	Turn-off time	t <sub>off</sub>	Duty ≤ 1%, t <sub>W</sub> = 10 μs	_	40	_		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 34 \text{ A}$	_	36	_	-	
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, V_{D} = 34 \text{ A}$	_	19	_		
Gate-source char	rge 1 (	Q <sub>gs1</sub>		_	8.1	_	nC	
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx 24 \text{ V, V}_{GS} = 10 \text{ V, I}_{D} = 34 \text{ A}$	_	4.8	_		
Gate switch char	ge (7/	Q <sub>SW</sub>		_	8.6	_		

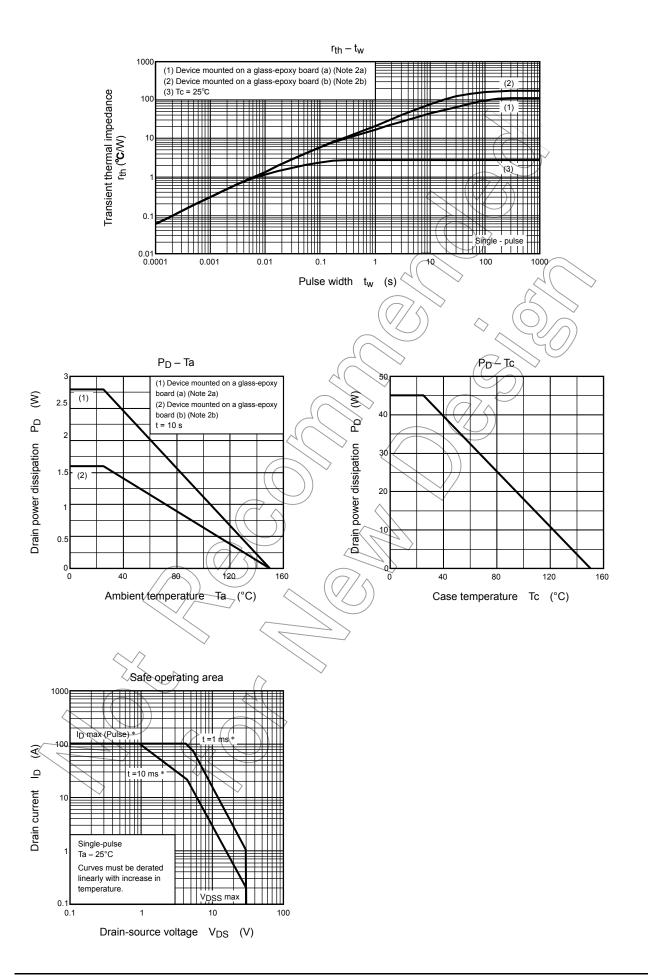
## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I <sub>DRP</sub>	_	_	_	102	Α
Enquard voltage (diade)	() <sub>1</sub>	I <sub>DR</sub> = 1 A, V <sub>GS</sub> = 0 V	_	- 0.4	- 0.6	V
Forward voltage (diode)	VDSF	$I_{DR} = 34 \text{ A}, V_{GS} = 0 \text{ V}$			- 1.2	V

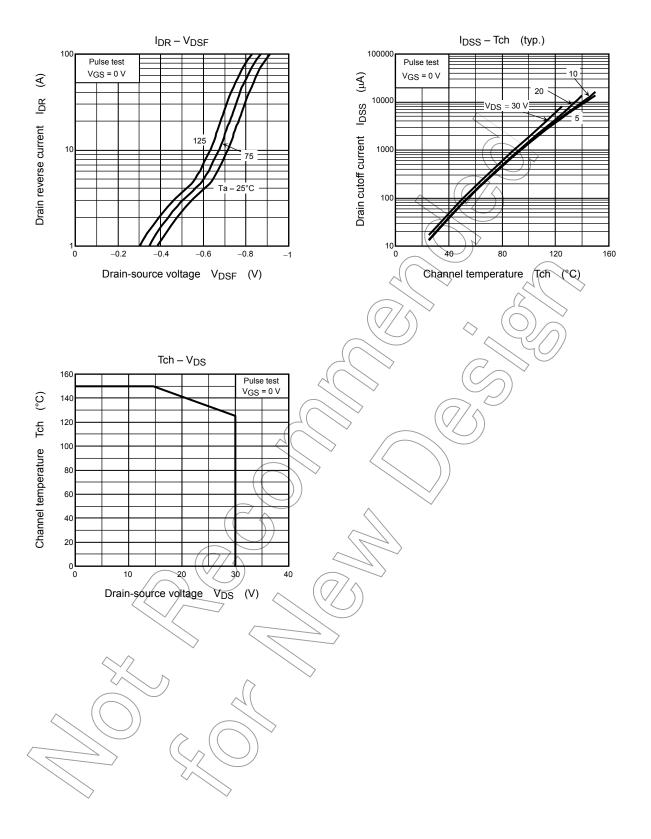




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